Modeling Hole Transport on the Surface of Ge Gamma-Ray Detectors

Nuclear Physics SBIR/STTR Exchange Meeting, September 13-14, 2010

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This work was supported by DOE SBIR Phase II Award No. DE-FG02-07ER84758 Office of Nuclear Physics



Outline

- Background
- Phase II objectives
- Work so far and results
- Conclusions
- Current and future work





•Used for in-beam nuclear structure studies

- •28 segmented HPGe detectors
- •~ 1π steradians
- •3D position sensitive (~1mm) detector
- •Completion in 2011



•Predecessor to GRETA



Segmented GRETINA Detector

High spatial resolution of γ-ray interactions



- Detector composed of 36-fold segmented Germanium crystals.
- Incoming gamma rays create electron/hole pairs via Compton scattering.
- In crystal bulk, simple valence band models yield highly accurate values for hole drift/diffusion coefficients (~1-2% error)
- Behavior along surfaces is highly pathological.



GRETINA Modeling Framework



Current modeling effort : encapsulate this infrastructure within VORPAL



Pathological Surface Signals

Consider a simpler Germanium PPC detector



-20

-30

0 10

Manufactured by

PHDs Co.

Fields calculated with spatially uniform negative surface charge distribution on nonpassivated face. Overlaid are hole trajectories associated with a range of interaction positions. Calculations of the electric field within the PPC detector at (a) 300 V below depletion, (b) depletion and (c) 200 V above depletion.



Pathological Surface Signals (continued)



Example of anomalous signal recorded when PPC detector was operated close to depletion.

Regions of the pulse shape have been highlighted to show the key features. For comparison, a signal representing the typical response of the PPC detector is overlaid (dashed blue line).

- A : Normal Bulk Charge motion
- B : Plateau for ~500 ns
- C : Acceleration (still impaired motion)
- D : Pulse reaches a maximum





Surface Drift Velocity Estimation



- Histogram of radial drift velocity estimated from one thousand anomalous events.
- Guassian fit to the data yields a mean value of 0.0025 (±0.0011) mm/ns, or 2500 m/s
- A factor of 40 slower than the accepted value for hole drift in bulk HPGe
- Means timing characteristics of interactions near surface MUCH different than those in the bulk
- Need to model/understand near surface transport



We have three technical objectives in the Phase II project whose feasibility has been demonstrated in the Phase I project.

Objective 1: Demonstrate the ability to accurately model carrier mobility in the crystal bulk. (Done—will show results)

Objective 2: Demonstrate the ability to accurately compute the electric field around the passivated surface. (currently at ORNL, moving to VORPAL)

Objective 3: Develop a more accurate determination of the gamma ray event location near the non-passivated surface. (Rest of this talk)

Valence Band Structure for Monte Carlo Simulations

- Band structure incorporated in dispersion relation:
- Determines energy vs. velocity and group velocity for MC simulations
- Analytic models (Warped, Parabolic, Elliptic, etc.)
 - •Straight forward to compute scattering probabilities between crystal and particle
 - Can include binary interactions: carrier-carrier scattering in a straightforward manner
 - Models have small range of validity in energy domain around the band maxima (valence) or minima (conduction)
- Numerical models (e.g., k.p and full band)
 - Wider range of validity in energy domain
 - Scattering probabilities are far more computationally intensive
- Numerical models may be necessary on surfaces where band structure is complicated, e.g., sub-band splitting due to surface electronic structure (confinement), surface E-fields, 2D DOS, etc.

Warped Band Model (3D)

• Classical simple model of the heavy/light hole

$$\epsilon(\mathbf{k}) = \frac{\hbar^2 |A|}{2m} k^2 [1 \mp g(\theta, \psi)]$$

- Model calculations depends on crystal properties, e.g., material speed of sound, temperature, density, etc.
- Cyclotron resonance experiments are used to determine band parameters.
- Density of states calculations shows that heavy hole has ~95% occupation, the light hole has ~5% occupation, and the spin orbit has ~0.01% occupation
- For high field setting, can improve results by considering interband transitions and including non-parapolic effects

Warped Band Model (cont.)

Using a single heavy hole (including non-parabolicity) can yield highly accurate values for the bulk drift velocity.



• Model can also give accurate computations of hole transverse and longitudinal diffusion

Surface Valence Band Models

- Very hard to calculate the valence band structure accurately in surface inversion layers
- Couple Schrodinger and Poisson (in surface normal direction) in order to get dispersion relation:

$$[H(\vec{K},k_z) + IV(z)]\psi_{\vec{K}}(z) = E(\vec{K})\psi_K(z)$$

$$\partial_z^2 V_H(z) = -\frac{e^2}{\epsilon_g} [\rho(z) - \rho_e z + N_D(z)]$$

- Use "triangular-well" approximation: $V(z) = eF_s z$
- Works well for Si (Fischetti et al., J. App. Phys., 2003)
- After calculating scattering probabilities, use Monte-Carlo to model hole motion.

Surface Valence Band Models

(Fischetti et al., J. App. Phys., 2003)





- Surface potential gives rise to band splitting
- Phonons can scatter holes into various subbands

A Simple Surface Valence Band Model (2D)

• Consider the 3D warped band model evaluated at: $\theta = \pi/2$

$$\epsilon(\mathbf{k}) = \frac{\hbar^2 |A|}{2m} k^2 [1 \mp g(\theta, \psi)]$$

- This assumes a surface normal of 100 (100 and 010) are equivalent
- Calculate scattering probabilities in 2D (use 2D DOS)
- E.g., acoustic phonons give:

$$P(\vec{k},\vec{k}') = \frac{\pi q \zeta^2}{4V\rho u} \binom{N_q}{N_q+1} (1+3\cos^2(\theta))\delta[\varepsilon(\vec{k}') - \varepsilon(\vec{k}) \mp \hbar q u]$$

$$P(\vec{k},\psi') = \int P(\vec{k},\vec{k}')k'dk'$$

$$V = (2\pi)^2 \Delta$$
TECH-X CORPORATION



- Optical emission has an absolute cutoff
- Effect from surface roughness is small

TECH

Simple Surface Valence Band Model

• Drift velocity shows substantial changes.



• PPC detector surface radial E-field 125 V/cm; Vd=2.5*10^5 cm/s TECH-X CORPORATION





- Reduction in surface mobility because of fundamental changes in phonon scattering
- Surface effects change with delta (for model considered here).
- Simple models can yield insight into the surface behavior

Current and future work

- Implementing interband scattering between heavy and light bands
- Integrating more accurate band non-parabolicity for simple warped band model (energy dependent effective mass)
- Developing surface subband calculations (triangular well appx) for Ge and coupling into Monte Carlo simulations (VORPAL)
- Need to validate results with more experimental data to from PPC and GRETINA detectors
- Overall result will be → better signal modeling for GRETINA=better resolution = better physics